isc Silicon PNP Power Transistor 2SA965

DESCRIPTION

- Power amplifier applications
- Driver stage amplifier applications
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for Switching and amplification

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-0.8	A
P_C	Collector Power Dissipation @ T_a<50℃	-0.9	W
$_J$	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEO}	Collector-base breakdown Voltage	I_C= -10mA; I_E= 0	-120			V
V_{EBO}	Emitter-base breakdown Voltage	I_E= -1mA; I_C= 0	-5			v
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -500mA; I_B= -50mA			-1.0	V
$V_{BE(on)}$	Base-Emitter on Voltage	V_{CE} = -5V, I_C= -500mA			-1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -120V; I_E= 0			-100	nA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-100	nA
h_{FE}	DC Current Gain	I_C=-100mA ; V_{CE}= -5V	-80		-240	

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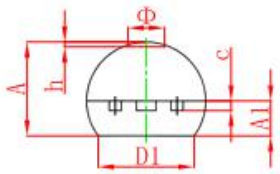
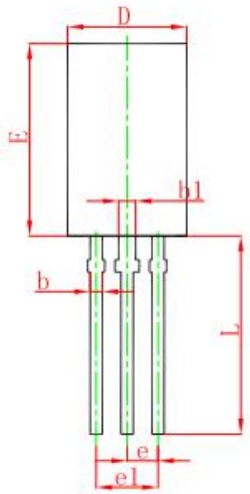
TO-92MOD Package Outline Dimensions





Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.800	5.000	0.189	0.197
A1	1.730	2.030	0.068	0.080
b	0.440	0.600	0.017	0.024
b1	0.940	1.100	0.037	0.043
c	0.350	0.450	0.014	0.018
D	5.900	6.100	0.232	0.240
D1	4.000		0.157	
E	8.500	8.700	0.335	0.343
e	1.500 TYP.		0.059 TYP.	
e1	2.900	3.100	0.114	0.122
L	13.800	14.200	0.543	0.559
Φ		1.600		0.063
h	0.000	0.380	0.000	0.015